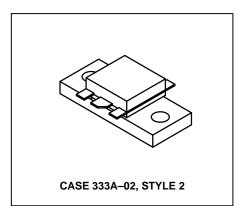
The RF Line **UHF Power Transistor**

The TP3061 is designed for 960 MHz mobile base stations in both analog and digital applications. It incorporates high value emitter ballast resistors, gold metallizations and offers a high degree of reliability and ruggedness. Including double input and output matching networks, the TP3060 features high impedances and is easy to match.

- Motorola Advanced Amplifier Concept Package
- Oxynitride Passivation
- Specified 26 Volts, 960 MHz Characteristics
 Output Power = 45 Watts
 Minimum Gain = 8.0 dB
 Efficiency = 50%
- Circuit board photomaster available upon request by contacting RF Tactical Marketing in Phoenix, AZ.

TP3061

45 W, 960 MHz UHF POWER TRANSISTOR NPN SILICON



MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	VCER	40	Vdc
Collector–Base Voltage	V _{CBO}	48	Vdc
Emitter–Base Voltage	V _{EBO}	4.0	Vdc
Collector Current — Continuous	IC	10	Adc
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	175 1.0	Watts W/°C
Storage Temperature Range	T _{stg}	-65 to +150	°C
Operating Junction Temperature	TJ	200	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case (1) at 70°C Case	$R_{\theta JC}$	1.2	°C/W

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Breakdown Voltage (I _C = 60 mA, R _{BE} = 75 Ω)	V(BR)CER	40	1	1	Vdc
Emitter–Base Breakdown Voltage (I _C = 6.0 mAdc)	V(BR)EBO	3.5		_	Vdc
Collector-Base Breakdown Voltage (I _E = 60 mAdc)	V _(BR) CBO	48			Vdc
Collector–Emitter Leakage ($V_{CE} = 26 \text{ V}, R_{BE} = 75 \Omega$)	ICER			15	mA

NOTE:

(continued)

1. Thermal resistance is determined under specified RF operating condition.

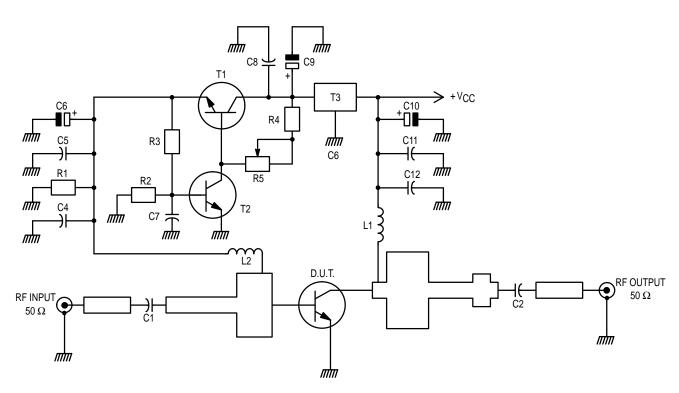


ELECTRICAL CHARACTERISTICS — **continued** (T_C = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Тур	Max	Unit
ON CHARACTERISTICS	•	•		•	
DC Current Gain (I _C = 1.0 Adc, V _{CE} = 10 Vdc)	hFE	15	_	100	_
DYNAMIC CHARACTERISTICS	•	•			
Output Capacitance (2) (V _{CB} = 26 V, I _E = 0, f = 1.0 MHz)	C _{ob}	45	60	_	pF
FUNCTIONAL TESTS	•	•		•	
Common–Emitter Amplifier Power Gain (V _{CC} = 26 V, P _{out} = 45 W, I _{CQ} = 200 mA, f = 960 MHz)	Gp	8.0	8.8	_	dB
Collector Efficiency (V _{CC} = 26 V, P _{out} = 45 W, f = 960 MHz)	η	50	53	_	%
Load Mismatch (V _{CC} = 26 V, P _{out} = 45 W, I _{CQ} = 200 mA, Load VSWR = 5:1, at all phase angles)	Ψ	No Degradation in Output Power Before and After Test		ver	
Overdrive (V _{CC} = 26 V, P _{in} = 15 W, f = 960 MHz)	OD	No Degradation in Output Power			

NOTE:

^{2.} Value of "Cob" is that of die only. It is not measurable in TP3061 because of internal matching network.



C1, C4, C7, C12 — Capacitor Chip 0805 330 pF 5%

C2 — Capacitor Chip 82 pF ATC

C5, C11, C8 — Capacitor Chip 0805 15 nF 5%

C6, C9, C10 — Capacitor Chip 0805 6.0, 8.0 μ F 35 V

L1, L2 — 1.5 Turns #18 AWG Choke

R1 — Chip Resistor 47 Ω 1206 5%

R2 — Chip Resistor 270 Ω 0805 5%

R3 — Chip Resistor 47 Ω 0805 5%

R4 — Chip Resistor 100 Ω 0805 5%

R5 — Trimmer 1.0 k Ω

T1 — SMD Transistor MJD31C or Similar

T2 — SMD Transistor

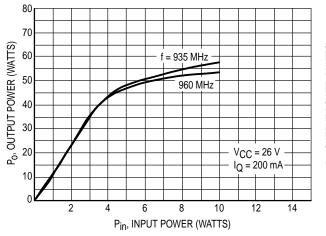
T3 — Voltage Regulator 7805

Board Material — 1/50", Teflon Glass, ε_{Γ} = 2.5,

Cu Clad 2 Sides, 35 μm Thick

Figure 1. 960 MHz Test Circuit

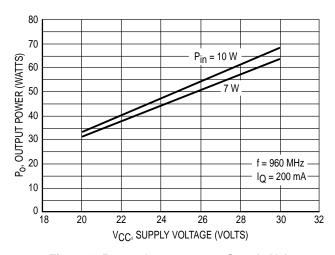
TYPICAL CHARACTERISTICS



80 70 $P_{in} = 10 W$ P₀, OUTPUT POWER (WATTS) 7 W $V_{CC} = 26 \text{ V} - 100 \text{ M}$ 10 0 880 900 920 940 960 980 1000 f, FREQUENCY (MHz)

Figure 2. Output Power versus Input Power

Figure 3. Output Power versus Frequency



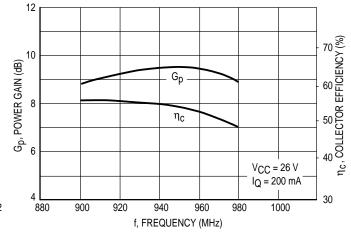
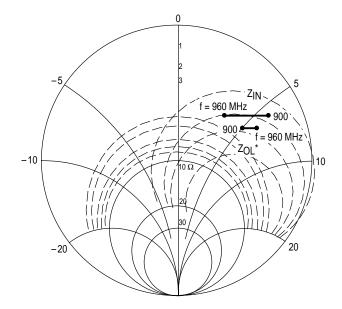


Figure 4. Power Output versus Supply Voltage

Figure 5. Typical Broadband Circuit Performance



$P_{Out} = 45 \text{ W} V_{CE} = 26 \text{ V}$			
f MHz	Z _{IN} OHMS	Z _{OL} * OHMS	
850	_	-	
900	2.8 + j6	4.1 + j5	
950	3.95 + j3.55	3.7 + j5.2	

ZOL* = Conjugate of the optimum load impedance. Into which the device operates at a given output power, voltage, and frequency.

Figure 6. Series Equivalent Input/Output Impedances

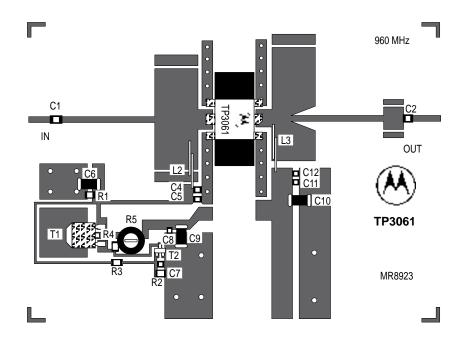
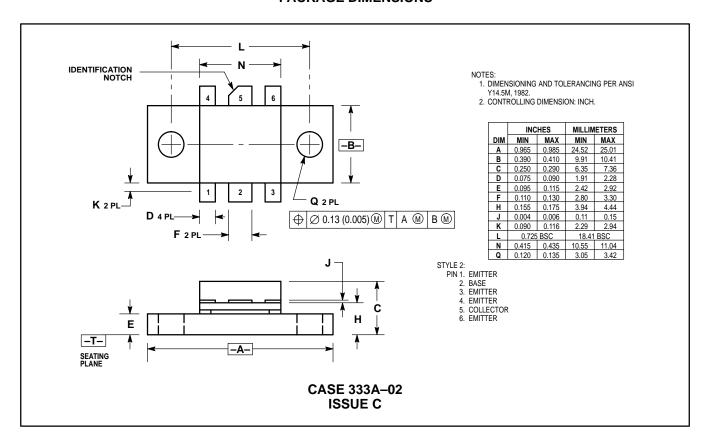


Figure 7. Test Circuit — Component Locations

PACKAGE DIMENSIONS



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